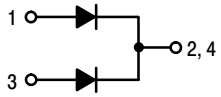
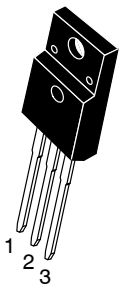
Switch-mode Power Rectifier 150 V, 20 A

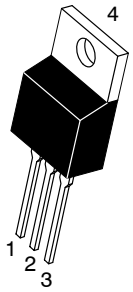
MBRF20H150CTG, MBR20H150CTG

SCHOTTKY BARRIER RECTIFIER 20 AMPERES, 150 VOLTS





TO−220 FULLPAK™
CASE 221D



TO−220
CASE 221A
STYLE 6

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 20 A Total (10 A Per Diode Leg)
- Guard−Ring for Stress Protection
- These Devices are Pb−Free and are RoHS Compliant

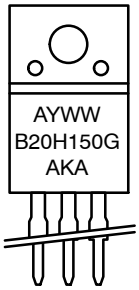
Applications

- Power Supply − Output Rectification
- Power Management
- Instrumentation

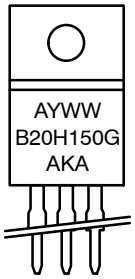
Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO−220 & TO−220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

MARKING DIAGRAMS



TO−220



TO−220FP

A	= Assembly Location
Y	= Year
WW	= Work Week
B20H150	= Device Code
G	= Pb−Free Device
AKA	= Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 2.

MAXIMUM RATINGS (Per Diode Leg)

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V_{RRM} V_{RWM} V_R	150	V
Average Rectified Forward Current (Rated V_R) T_C = 134°C	(Per Leg) (Per Device)	$I_{F(AV)}$	10 20	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	180	A
Operating Junction Temperature (Note 1)		T_J	−20 to +150	°C
Storage Temperature		T_{stg}	−65 to +150	°C
Voltage Rate of Change (Rated V_R)		dv/dt	10,000	V/μs
ESD Ratings:	Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Rating		Symbol	Value	Unit
Maximum Thermal Resistance (MBR20H150CTG) (MBRF20H150CTG)	 − Junction−to−Case − Junction−to−Ambient − Junction−to−Case	 $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JC}$	 2.0 45 2.5	°C/W

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) (I_F = 5 A, T_C = 25°C) (I_F = 5 A, T_C = 125°C) (I_F = 10 A, T_C = 25°C) (I_F = 10 A, T_C = 125°C)	v_F	 0.72 0.57 0.87 0.65	 0.60 0.68	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, T_C = 25°C) (Rated DC Voltage, T_C = 125°C)	i_R		 50 30	 μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBR20H150CTG	TO−220 (Pb−Free)	50 Units / Rail

DISCONTINUED (Note 3)

MBRF20H150CTG	TO−220FP (Pb−Free)	50 Units / Rail

3. **DISCONTINUED:** This device is not recommended for new design. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

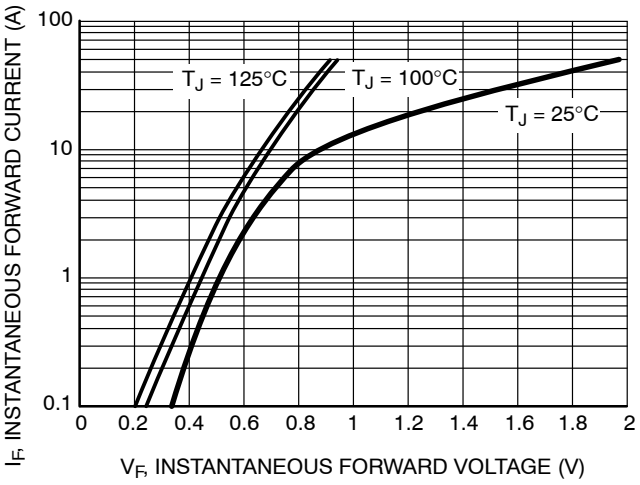


Figure 1. Typical Forward Voltage

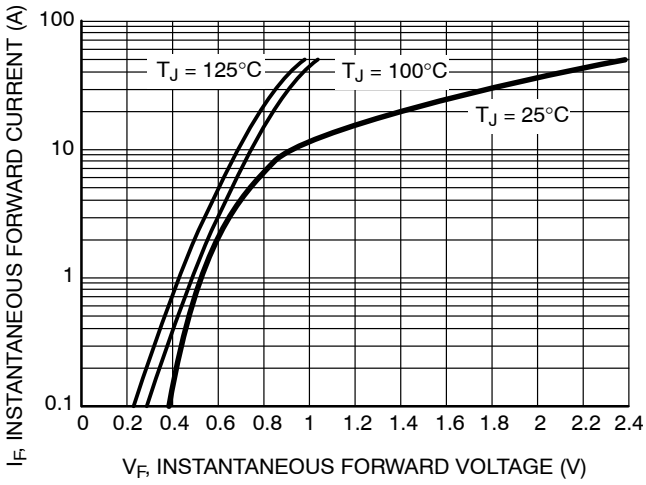


Figure 2. Maximum Forward Voltage

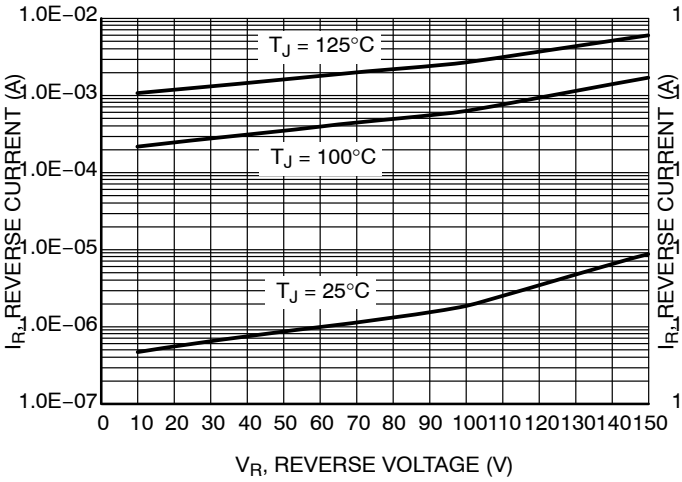


Figure 3. Typical Reverse Current

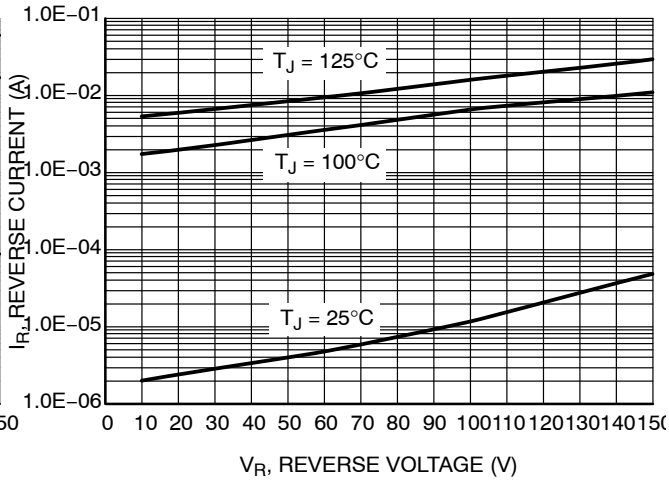


Figure 4. Maximum Reverse Current

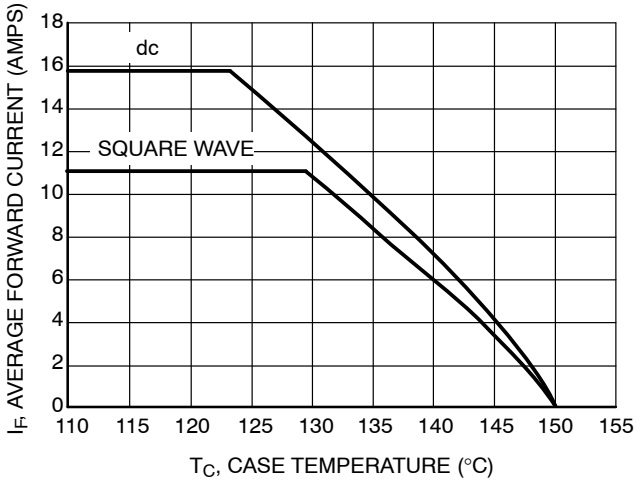


Figure 5. Current Derating

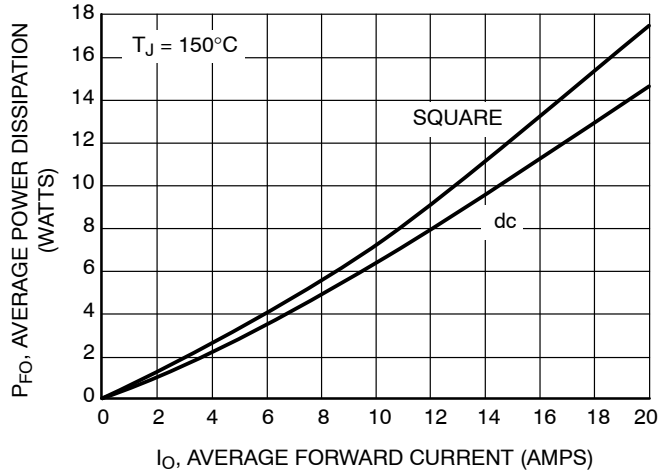


Figure 6. Forward Power Dissipation

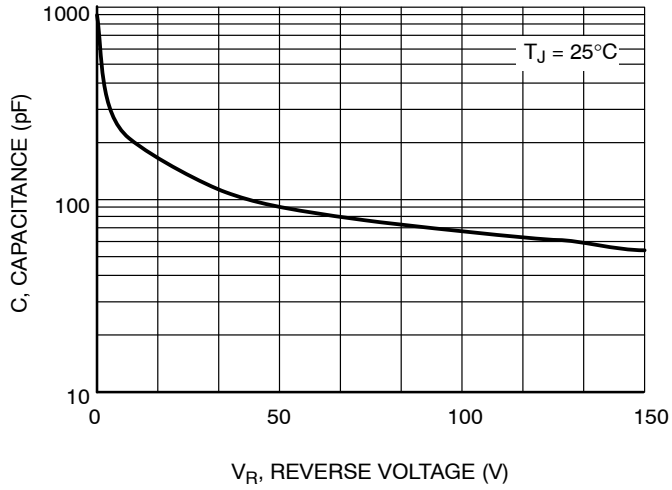


Figure 7. Capacitance

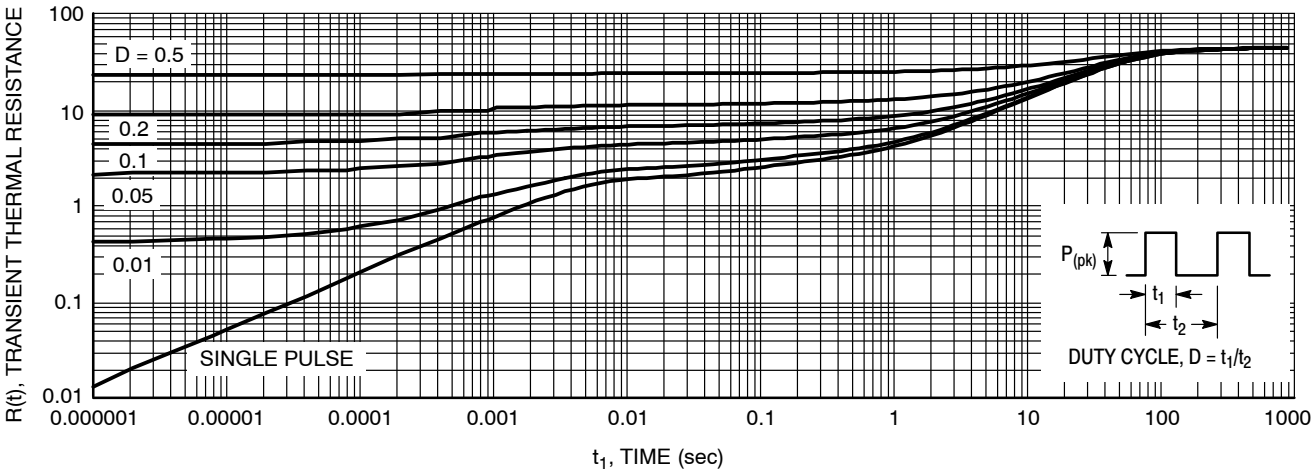


Figure 8. Thermal Response Junction−to−Ambient for MBR20H150CTG

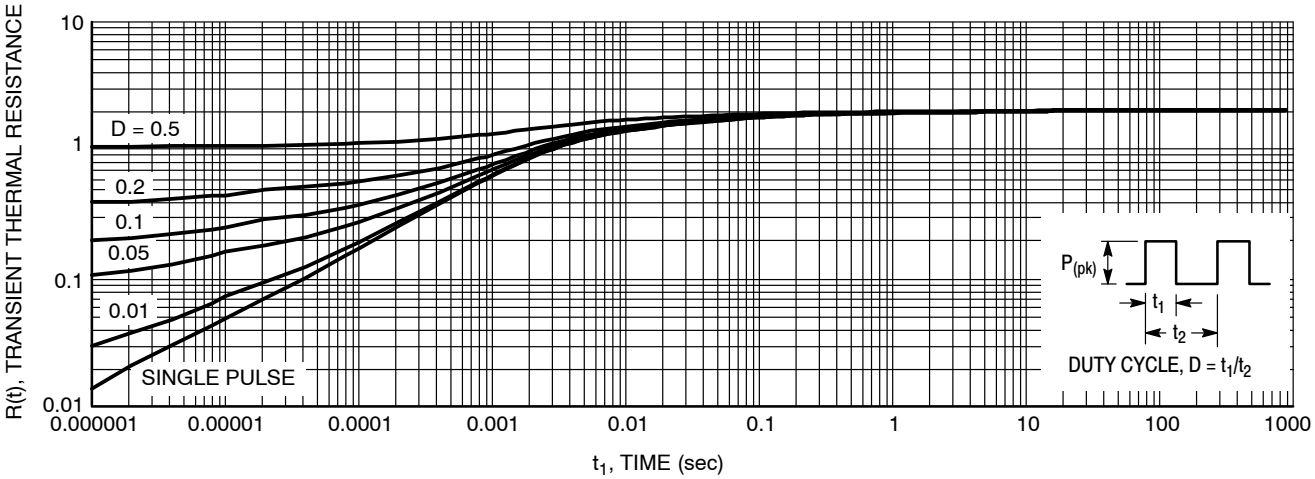


Figure 9. Thermal Response Junction−to−Case for MBR20H150CTG

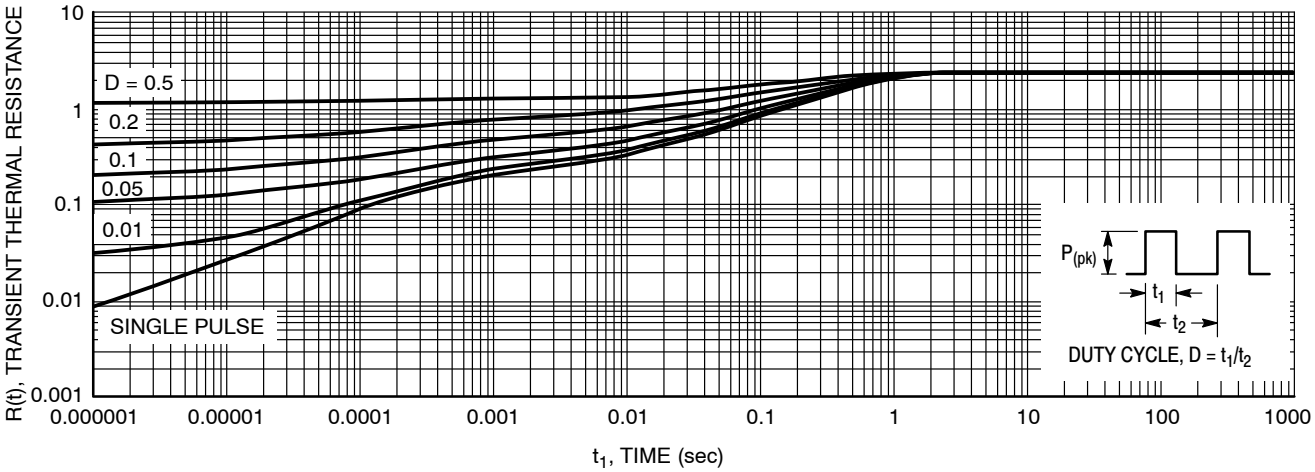


Figure 10. Thermal Response Junction−to−Case for MBRF20H150CTG

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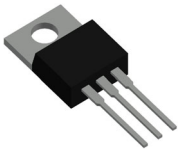
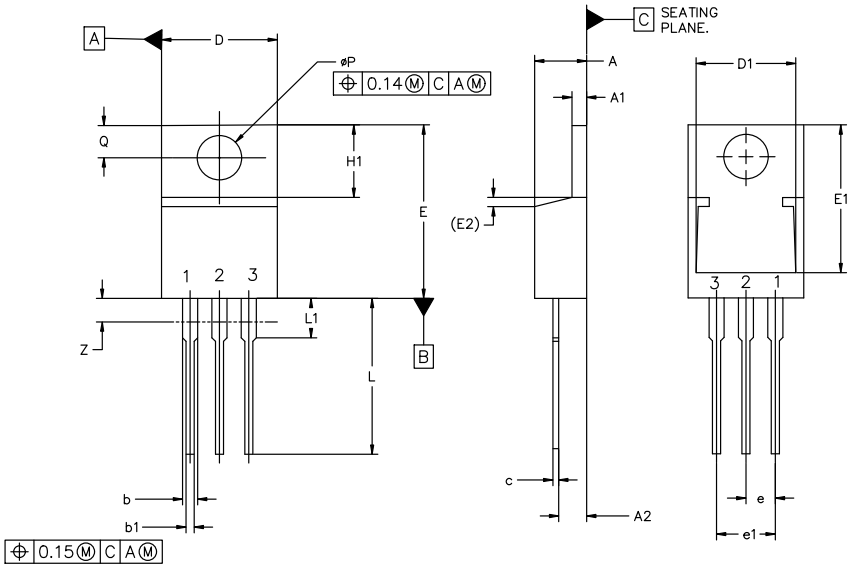


TO−220−3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025



MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.54	2.66
e1	4.83	5.08	5.33
H1	5.97	6.22	6.47
L	12.70	13.49	14.27
L1	2.80	3.45	4.10
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	−.−−	−.−−	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR
4. EMITTER

STYLE 3:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 4:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

STYLE 5:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE

STYLE 8:
PIN 1. CATHODE
2. ANODE
3. EXTERNAL TRIP/DELAY
4. ANODE

STYLE 9:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 10:
PIN 1. GATE
2. SOURCE
3. DRAIN
4. SOURCE

STYLE 11:
PIN 1. DRAIN
2. SOURCE
3. GATE
4. SOURCE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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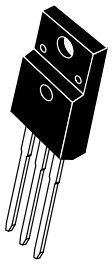
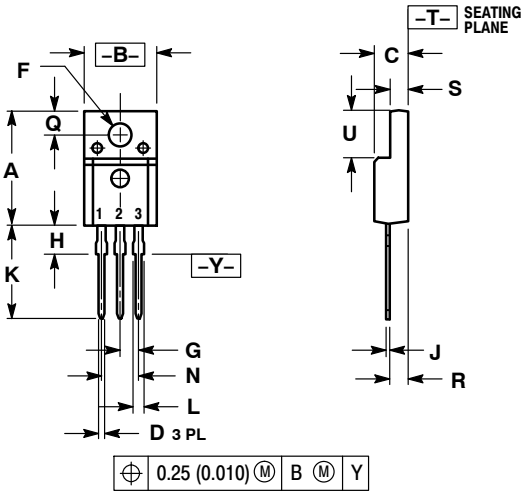


SCALE 1:1

TO−220 FULLPAK
CASE 221D−03
ISSUE K

DATE 27 FEB 2009



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. 221D−01 THRU 221D−02 OBSOLETE, NEW STANDARD 221D−03.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

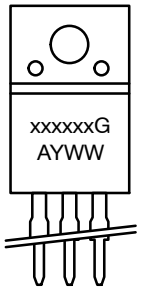
STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. CATHODE

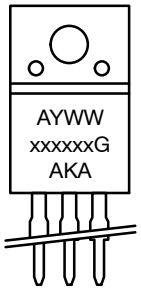
STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 6:
PIN 1. MT 1
2. MT 2
3. GATE

MARKING DIAGRAMS



Bipolar



Rectifier

xxxxxx	= Specific Device Code
G	= Pb−Free Package
A	= Assembly Location
Y	= Year
WW	= Work Week

A	= Assembly Location
Y	= Year
WW	= Work Week
xxxxxx	= Device Code
G	= Pb−Free Package
AKA	= Polarity Designator

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